40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET
POWERDI®

NEW PRODUCT

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
40V	2.5mΩ @ V_{GS} = 10V	100A
	4mΩ @ V_{GS} = 4.5V	100A

Features

- Rated to +175°C – ideal for high ambient temperature environments
- 100% Unclamped Inductive Switching – ensures more reliable and robust end application
- Low $R_{DS(ON)}$ – minimizes power losses
- Low Qg – minimizes switching losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

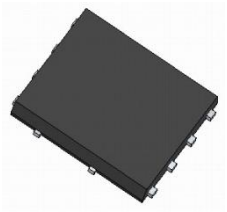
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

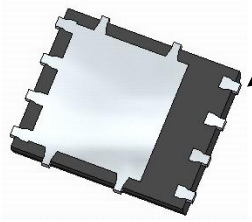
Mechanical Data

- Case: POWERDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

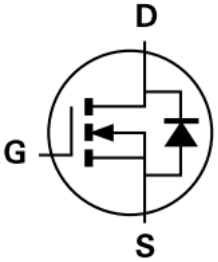
POWERDI®5060-8



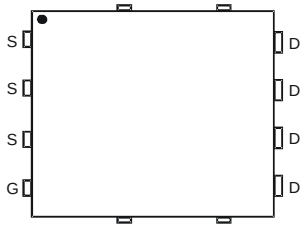
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4004LPS-13	POWERDI®5060-8	2,500 / Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

= Manufacturer's Marking
H4004LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 14 = 2014)
WW = Week (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5)	T_A = +25°C T_A = +70°C	I_D	26 21	A
Continuous Drain Current (Note 6)	T_C = +25°C T_C = +70°C (Note 8)	I_D	100 100	A
Maximum Continuous Body Diode Forward Current (Note 6)		I_S	70	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	100	A
Avalanche Current, L=0.2mH		I_{AS}	33.3	A
Avalanche Energy, L=0.2mH		E_{AS}	110	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	47	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	138	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	0.9	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	2.5	mΩ	V_{GS} = 10V, I_D = 50A
		—	—	4		V_{GS} = 4.5V, I_D = 50A
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	V_{GS} = 0V, I_S = 50A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	4508	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	1648	—		
Reverse Transfer Capacitance	C_{rss}	—	104	—		
Gate Resistance	R_g	—	0.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	34.6	—	nC	V_{DD} = 20V, I_D = 30A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	82.2	—	nC	
Gate-Source Charge	Q_{gs}	—	9.9	—		
Gate-Drain Charge	Q_{gd}	—	11.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.9	—	ns	V_{DD} = 20V, V_{GS} = 10V, I_D = 30A, R_G = 1.6Ω
Turn-On Rise Time	t_R	—	13.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	25.9	—		
Turn-Off Fall Time	t_F	—	7.9	—		
Body Diode Reverse Recovery Time	t_{RR}	—	48.4	—	ns	I_F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	72.4	—	nC	

Notes:
5. Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single- sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7 .Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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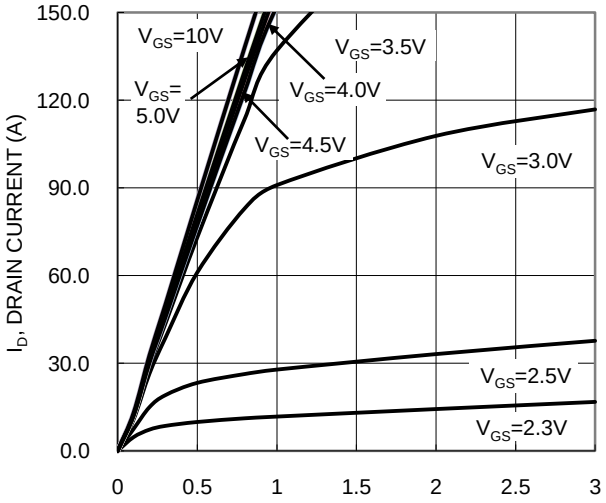

Figure 1. Typical Output Characteristic

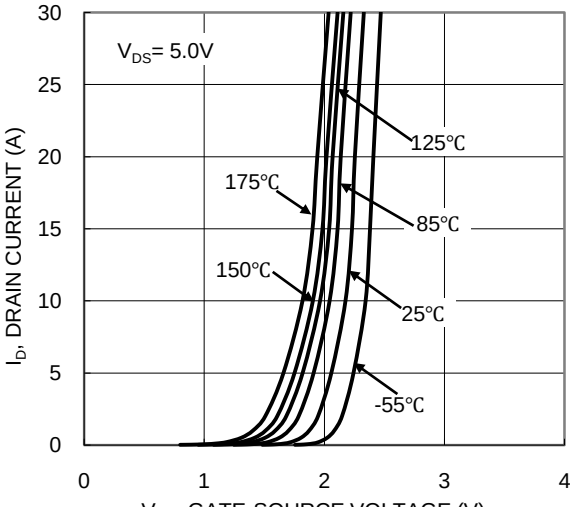

Figure 2. Typical Transfer Characteristic

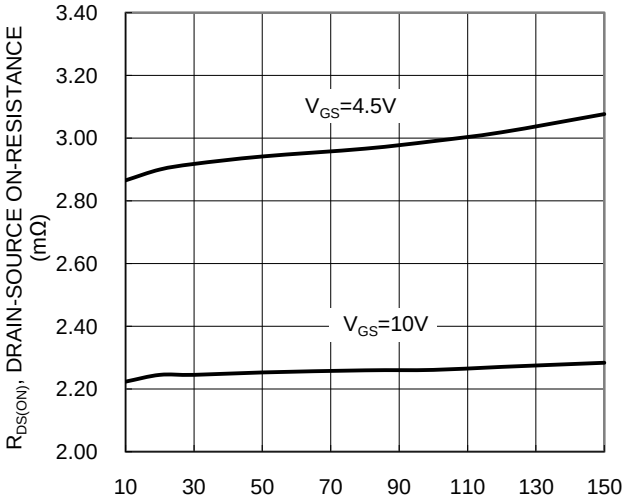

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

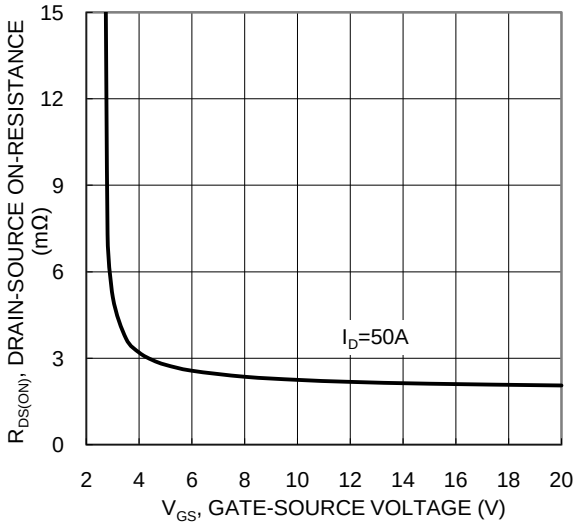

Figure 4. Typical Transfer Characteristic

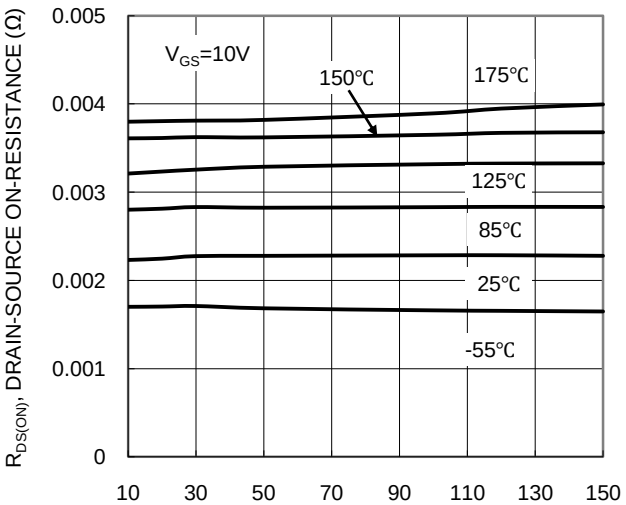

Figure 5. Typical On-Resistance vs. Drain Current and Temperature

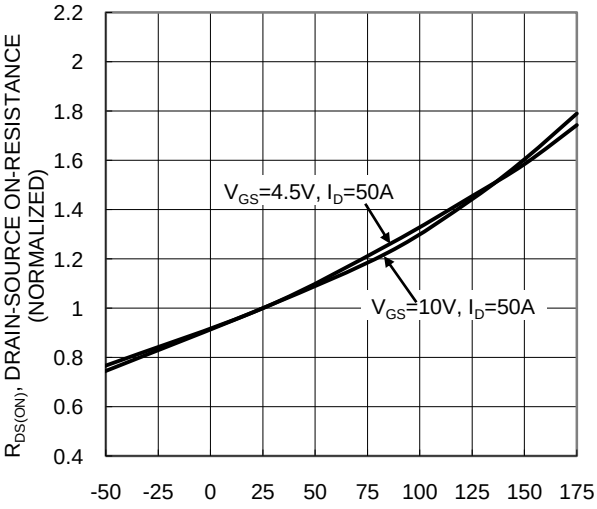

Figure 6. On-Resistance Variation with Temperature

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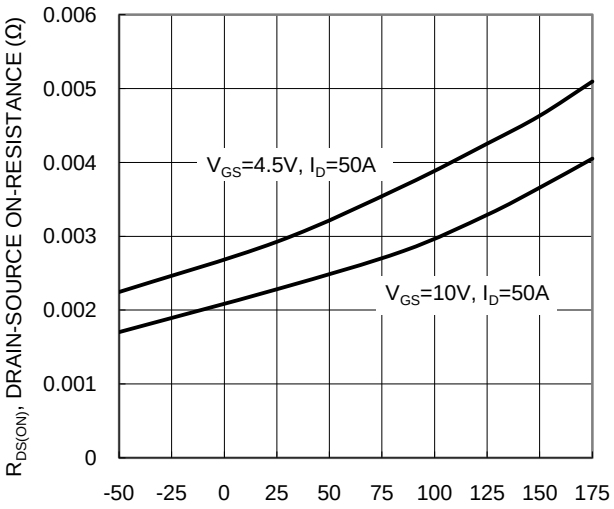

Figure 7. On-Resistance Variation with Temperature

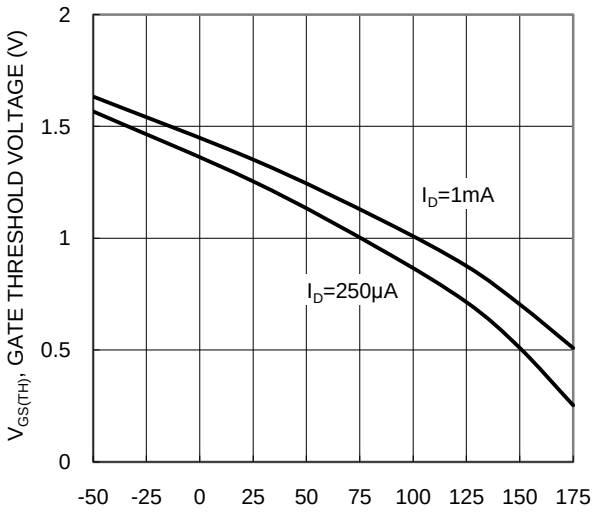

Figure 8. Gate Threshold Variation vs. Temperature

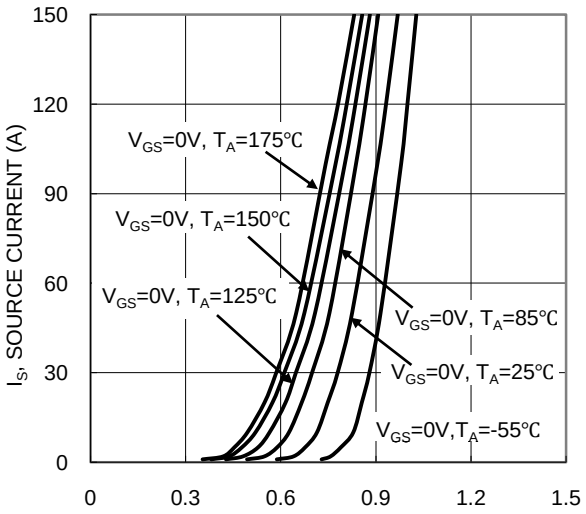

Figure 9. Diode Forward Voltage vs. Current

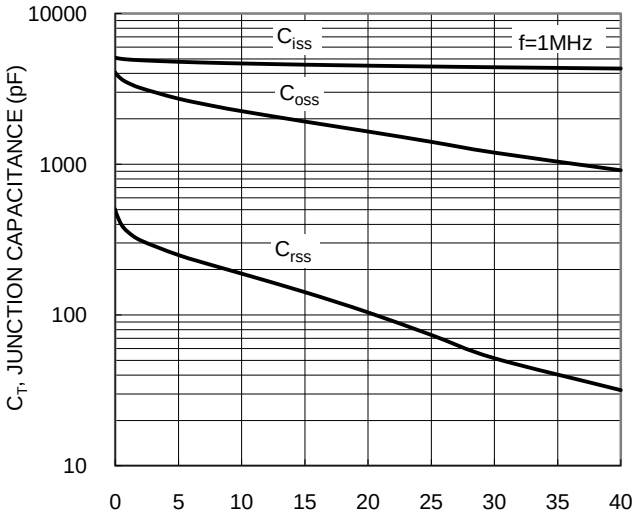

Figure 10. Typical Junction Capacitance

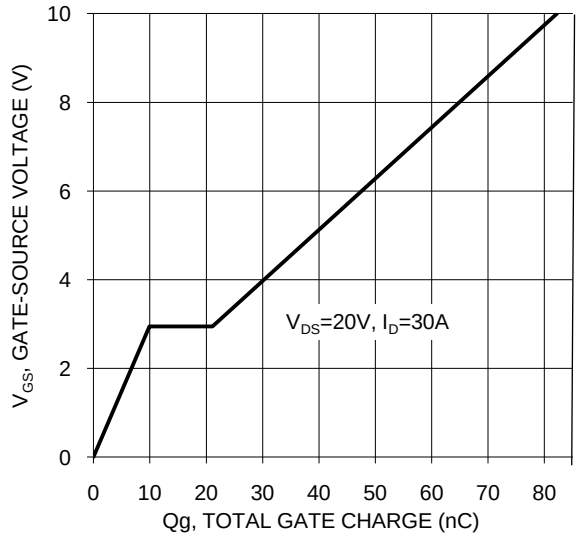

Figure 11. Gate Charge

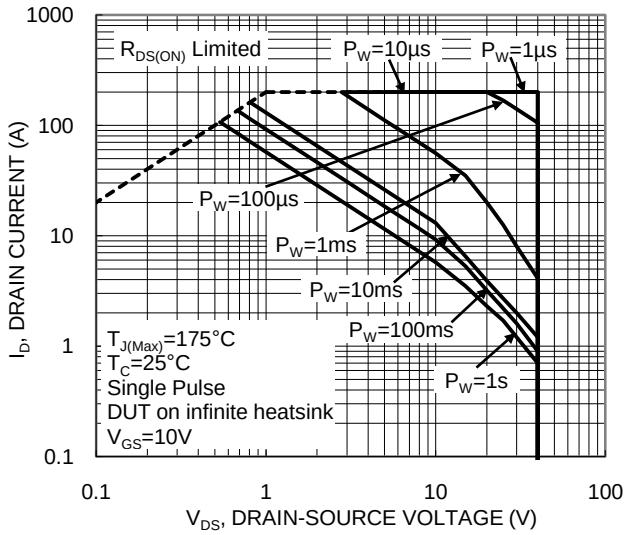

Figure 12. SOA, Safe Operation Area

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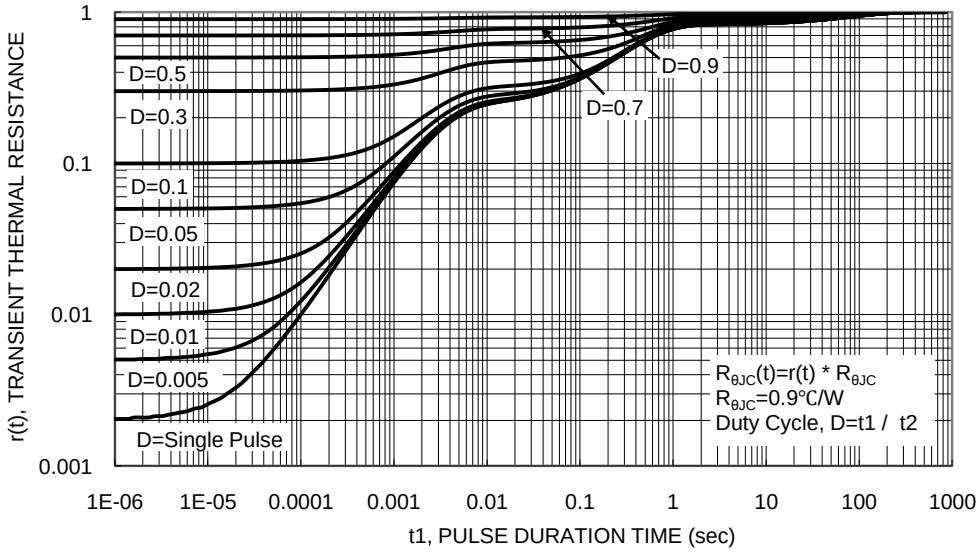
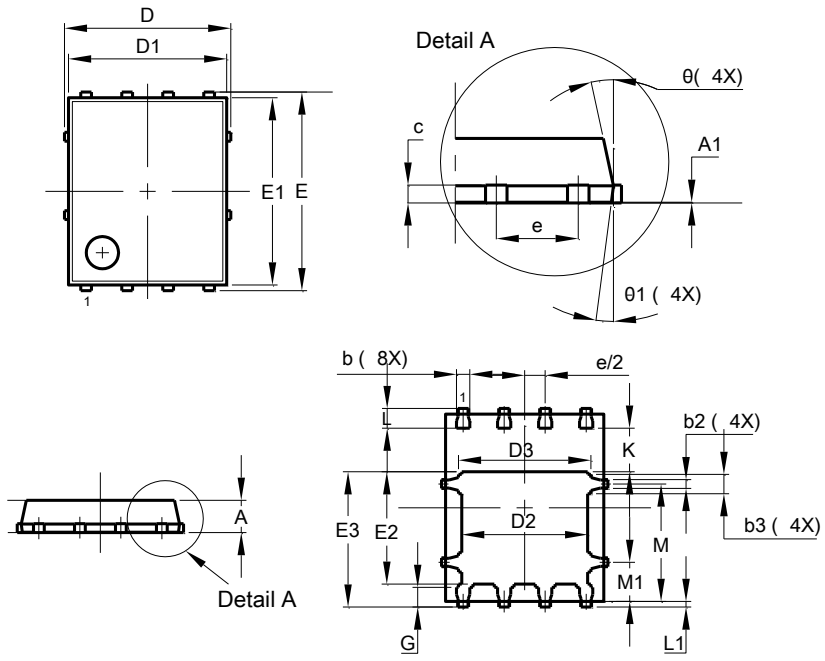


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI®5060-8			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

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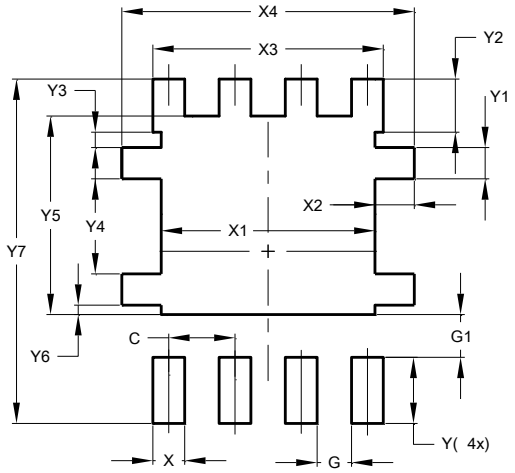
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

单击下面可查看定价，库存，交付和生命周期等信息

>>Diodes Incorporated(达迩科技（美台）)